
HZM6.8FA

Silicon Epitaxial Planar Zener Diode for Surge Absorb

HITACHI

ADE-208-442A(Z)

Rev 1

September 1996

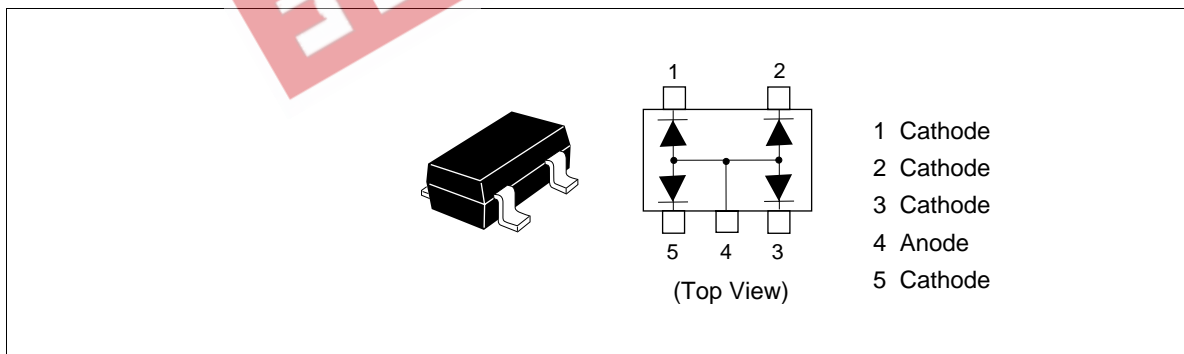
Features

- HZM6.8FA has four devices, and can absorb external + and -surge.
- MPAK-5 Package is suitable for high density surface mounting and high speed assembly.

Ordering Information

| Type No. | Laser Mark | Package Code |
|----------|------------|--------------|
| HZM6.8FA | 68A | MPAK-5 |

Outline



HZM6.8FA

Absolute Maximum Ratings (Ta = 25°C)

| Item | Symbol | Value | Unit |
|----------------------|-----------------|-------------|------|
| Power dissipation | Pd ¹ | 200 | mW |
| Junction temperature | Tj | 150 | °C |
| Storage temperature | Tstg | -55 to +150 | °C |

Note 1. Four device total, With P.C board.

Electrical Characteristics (Ta = 25°C) ^{*1}

| Item | Symbol | Min | Typ | Max | Unit | Test Condition |
|--------------------|----------------|------|-----|-----|------|---|
| Zener voltage | V _z | 6.47 | — | 7.0 | V | I _z = 5 mA, 40ms pulse |
| Reverse current | I _R | — | — | 2 | μA | V _R = 3.5V |
| Capacitance | C | — | — | 130 | pF | V _R = 0V, f = 1 MHz |
| Dynamic resistance | r _d | — | — | 30 | Ω | I _z = 5 mA |
| ESD-Capability | — | 30 | — | — | kV | C = 150pF, R = 330 Ω, Both forward and reverse direction 10 pulse ^{*2} |

Notes 1. Per one device.

2. Failure criterion ; IR > 2 μA at VR = 3.5V.

Main Characteristic

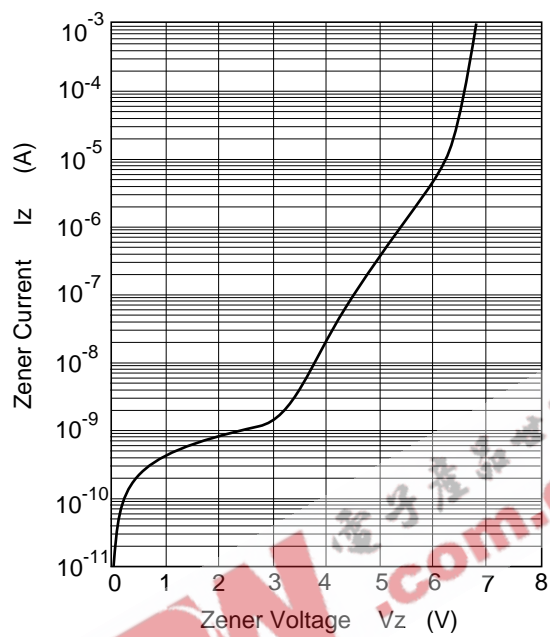


Fig.1 Zener current Vs. Zener voltage

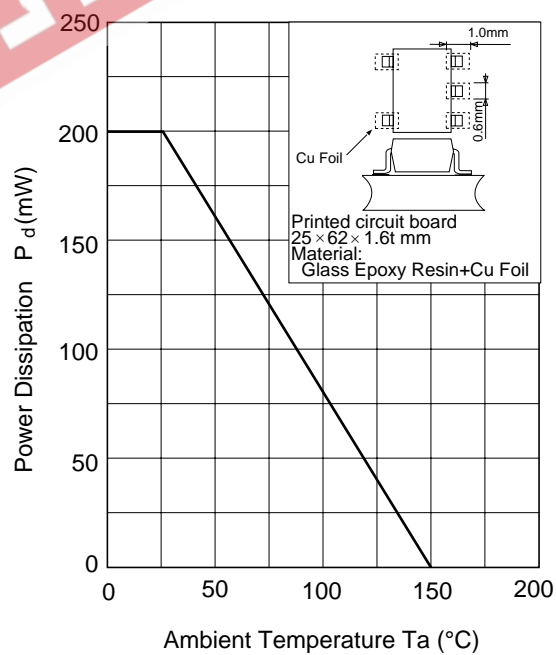
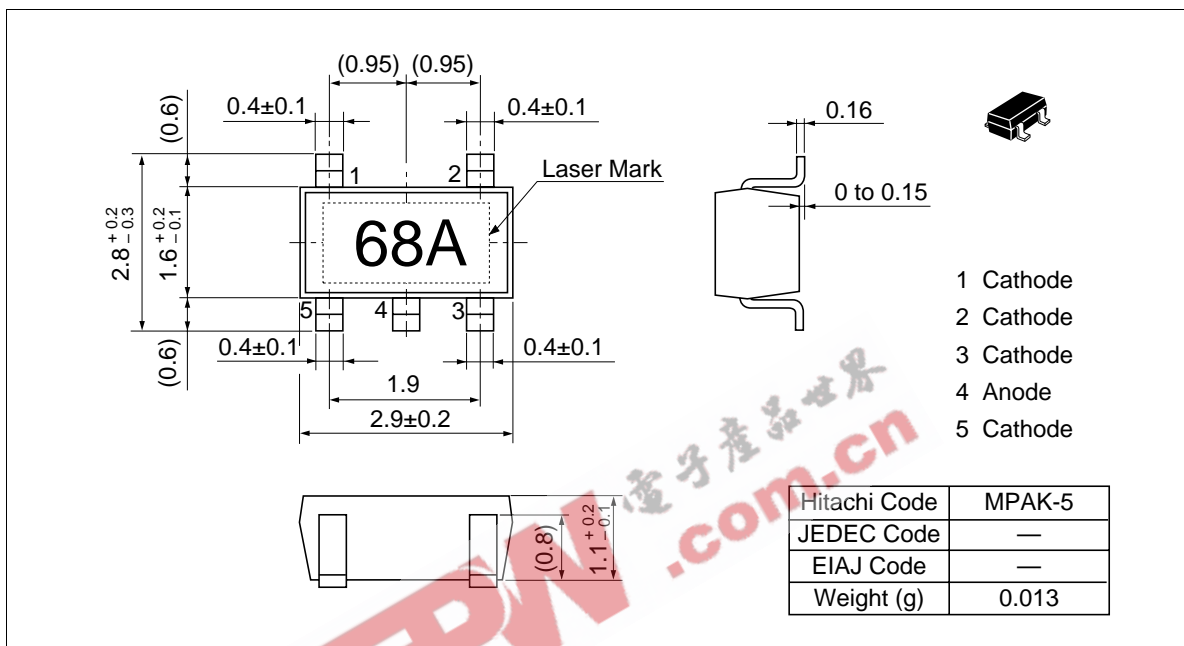


Fig.2 Power Dissipation Vs. Ambient Temperature

HZM6.8FA

Package Dimensions

Unit : mm



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